

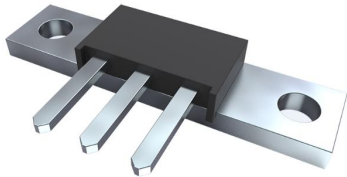
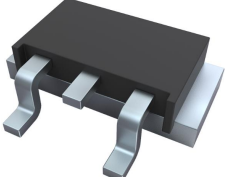
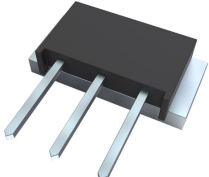
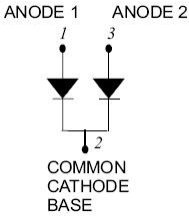
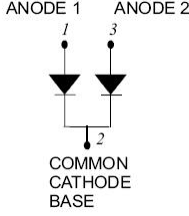
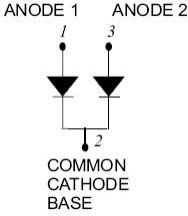
## 66CNQ200 SCHOTTKY RECTIFIER

### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features

- 175°C T<sub>J</sub> operation
- Center tap module
- Very Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Low profile, high current package
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

66CNQ200	66CNQ200SL	66CNQ200SM
		
		
<b>PRM3</b>	<b>PRM3-SL</b>	<b>PRM3-SM</b>

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	200	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> = 155°C, rectangular wave form	30(Per Leg)	A
			60(Per Device)	
Peak One Cycle Non-Repetitive Surge Current(Per leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	708	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per leg) *	V <sub>F1</sub>	@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.80	0.92	V
	V <sub>F2</sub>	@ 30A, Pulse, T <sub>J</sub> = 125 °C	0.63	0.72	V
Reverse Current (Per leg) *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.0002	1.5	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.28	21	mA
Junction Capacitance(Per leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	750	900	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

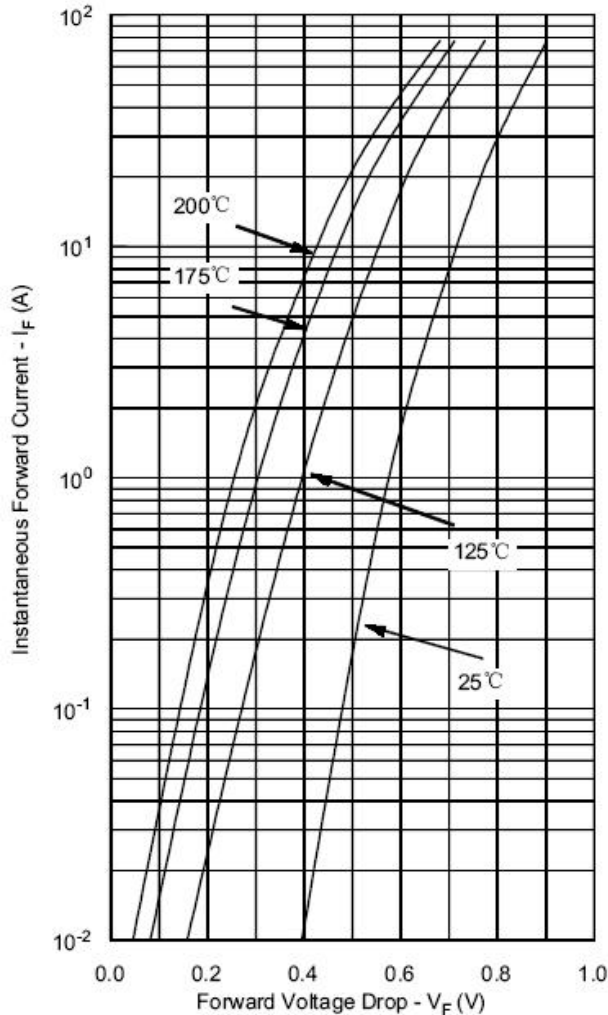
\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

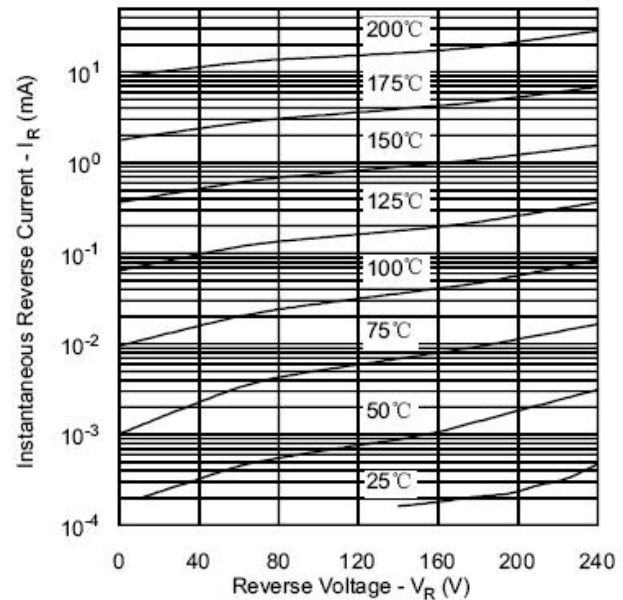
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case (per leg)	R <sub>θJC</sub>	DC operation	0.85	°C/W
Typical Thermal Resistance Junction to Case (per package)	R <sub>θJC</sub>	DC operation	0.42	°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.30	°C/W
Mounting Torque	TM	-	40(min)	Kg-cm
			58(max)	
Approximate Weight	wt	-	7.8	g
Case Style	PRM3 PRM3-SL PRM3-SM			

**Ratings and Characteristics Curves**

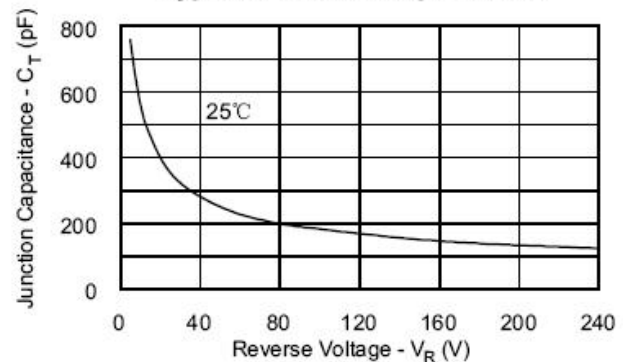
**Typical Forward Characteristics**



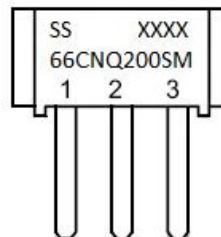
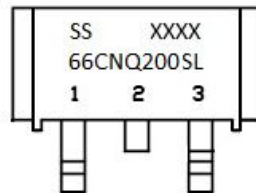
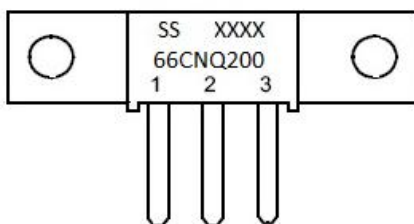
**Typical Reverse Characteristics**



**Typical Junction Capacitance**



**Marking Diagram**



Where XXXX is YYWW

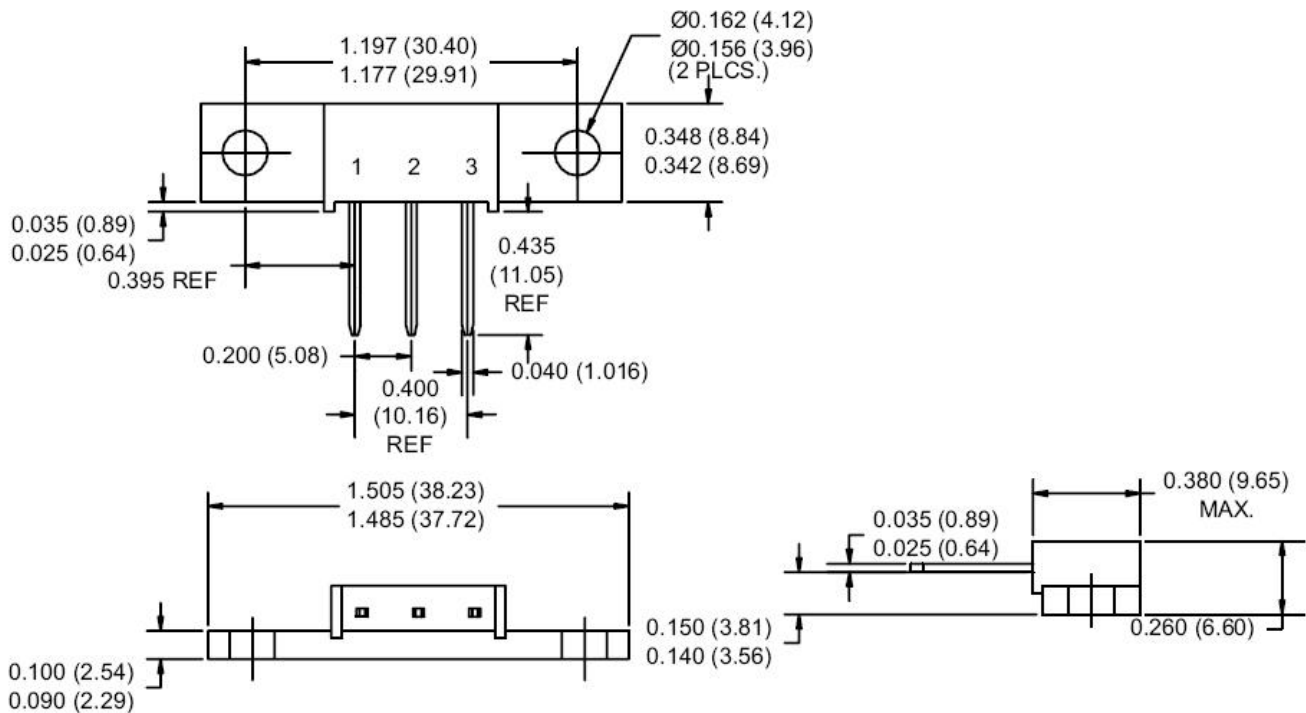
1st row SS YYWWL  
2nd row 66CNQ200/SL/SM  
3rd row 1 2 3 (pin)  
SS = SS  
YY = Year  
WW = Week

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

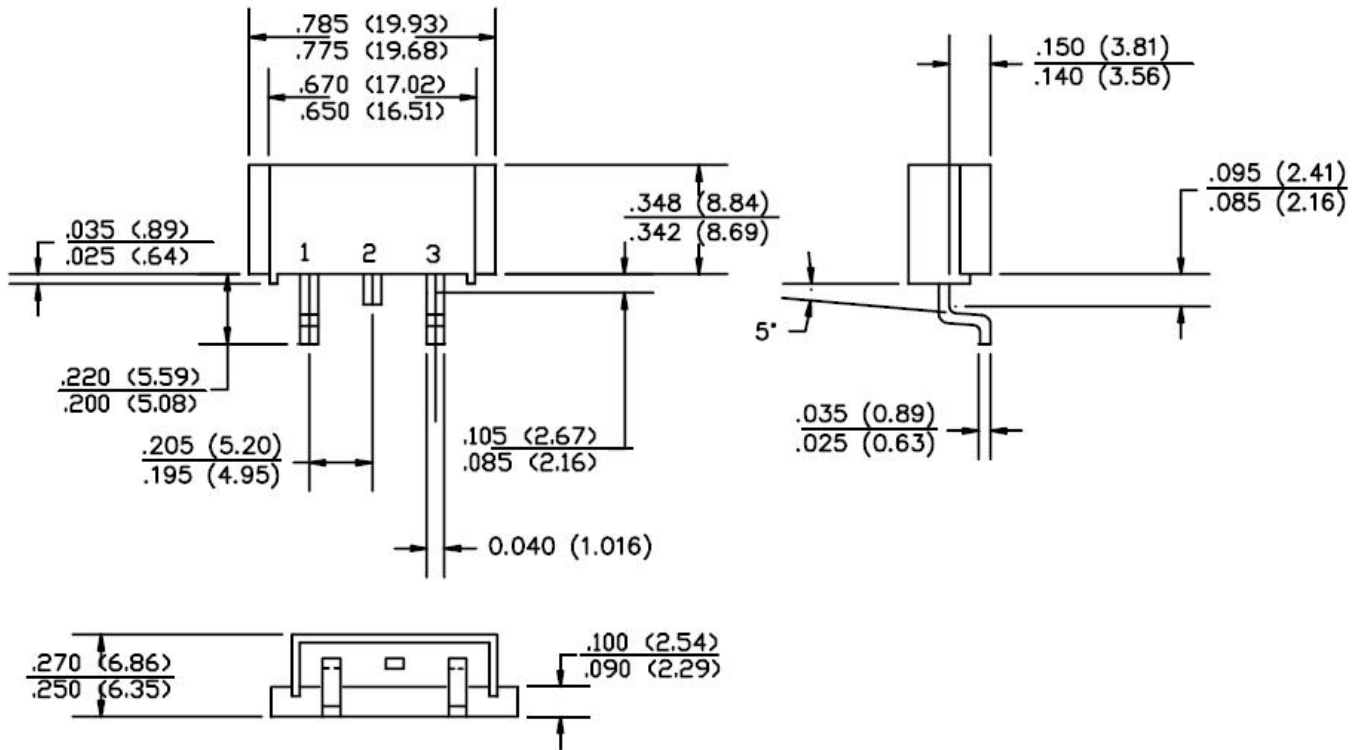
**Ordering Information**

Device	Package	Terminals finish	Shipping
66CNQ200	PRM3	Nickel plated	48pcs / box
66CNQ200S	PRM3	Pure Sn dipped (dipped height 6-8 mm)	48pcs / box
66CNQ200SL	PRM3-SL	Nickel plated	100pcs / box
66CNQ200SM	PRM3-SM	Nickel plated	48pcs / box

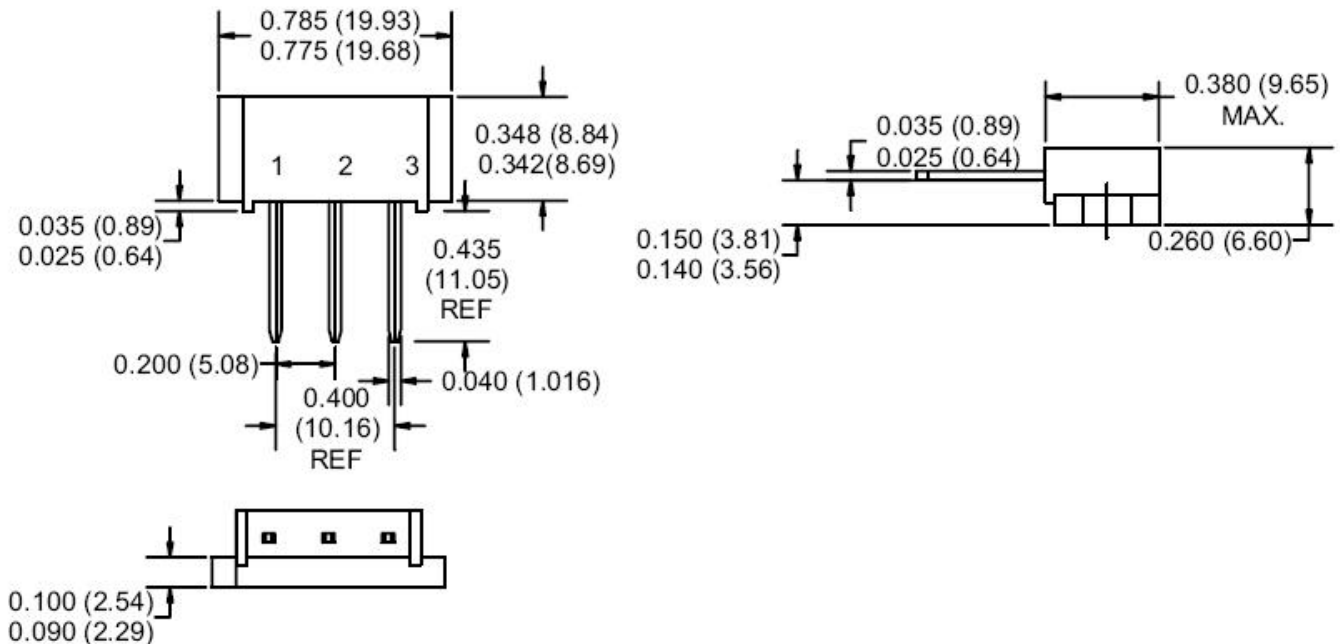
**Mechanical Dimensions PRM3 (Inches/Millimeters)**



**Mechanical Dimensions PRM3-SL (Inches/Millimeters)**



**Mechanical Dimensions PRM3-SM (Inches/Millimeters)**



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